

General Description

The SN2300A is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent $R_{DS(on)}$ and gate charge for most of the small power switching and load switch applications.

The SN2300A meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent C_{dv}/dt effect decline
- Green Device Available

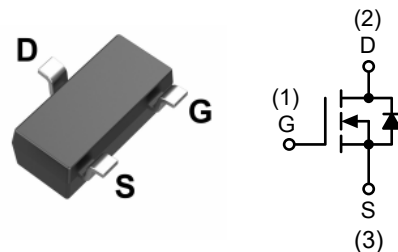
Product Summary

BV_{DSS}	$R_{DS(on)}$	I_D
20V	60m Ω	3.0A

Applications

- High Frequency Point-of-Load Synchronous Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-23L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	3.0	A
$I_D@T_C=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	2.5	A
I_{DM}	Pulsed Drain Current ²	10	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	1.0	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	200	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	75	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.024	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=4.5V$, $I_D=1.8A$	---	60	75	m Ω
		$V_{GS}=2.5V$, $I_D=1.5A$	---	70	85	
		$V_{GS}=1.8V$, $I_D=1A$	---	90	110	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	0.3	0.85	1.2	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-2.51	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=16V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=16V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 8V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=3A$	---	8.0	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	1.5	3.0	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=15V$, $V_{GS}=4.5V$, $I_D=1A$	---	5.4	---	nC
Q_{gs}	Gate-Source Charge		---	0.44	---	
Q_{gd}	Gate-Drain Charge		---	1.0	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=10V$, $V_{GS}=4.5V$, $R_G=3.3\Omega$ $I_D=1A$	---	1.5	---	ns
T_r	Rise Time		---	25.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	5.5	---	
T_f	Fall Time		---	16.8	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1MHz$	---	320	---	pF
C_{oss}	Output Capacitance		---	35	---	
C_{rss}	Reverse Transfer Capacitance		---	22	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	3.0	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	9.0	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=2A$, $dI/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	5.1	---	nS
Q_{rr}	Reverse Recovery Charge		---	1.5	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper , $t<10\text{sec}$.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

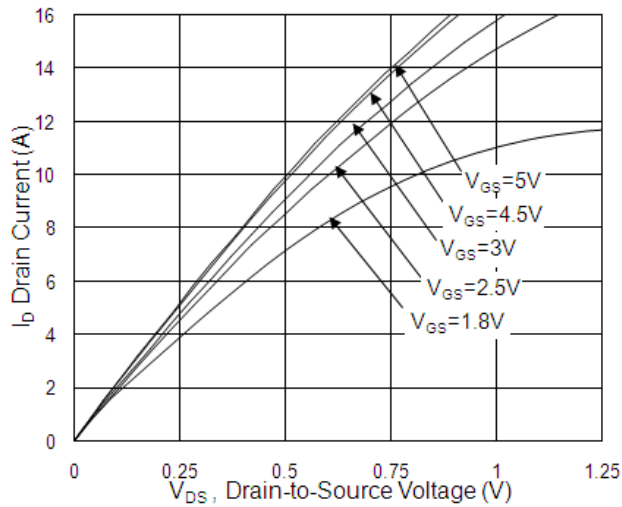


Fig.1 Typical Output Characteristics

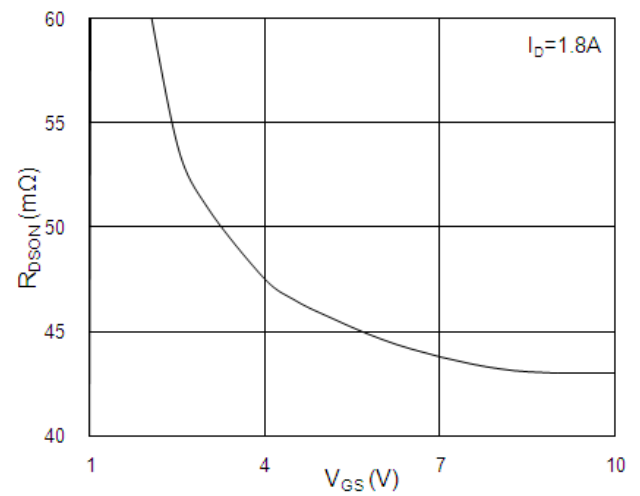


Fig.2 On-Resistance vs. Gate-Source

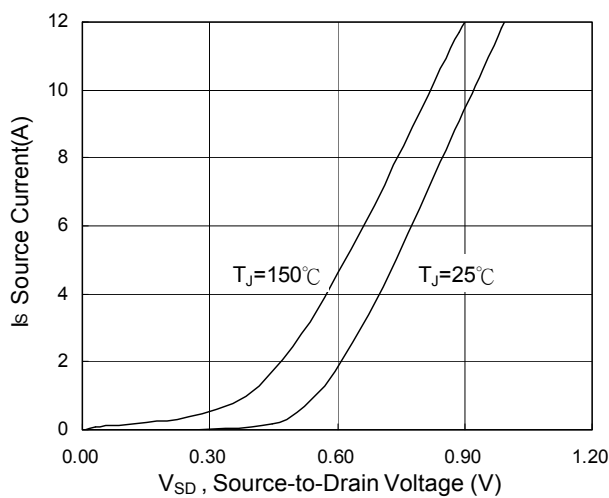


Fig.3 Forward Characteristics Of Reverse

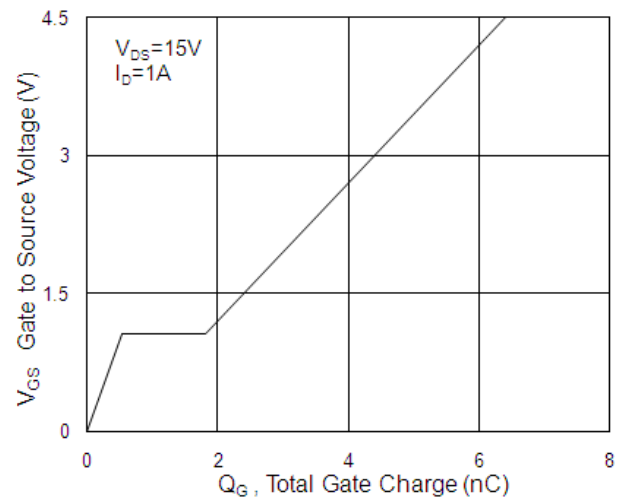


Fig.4 Gate-Charge Characteristics

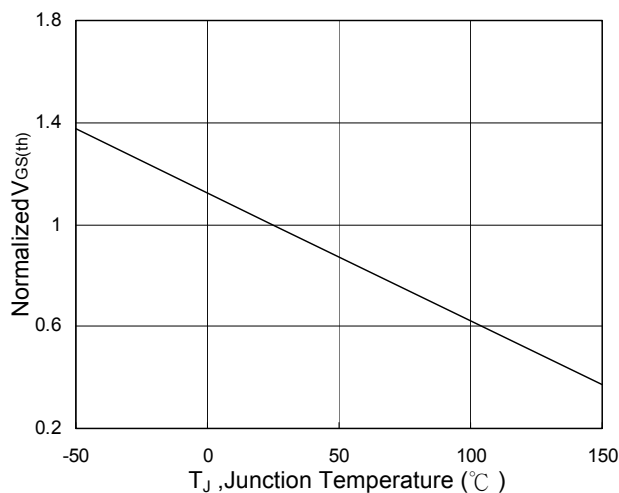


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

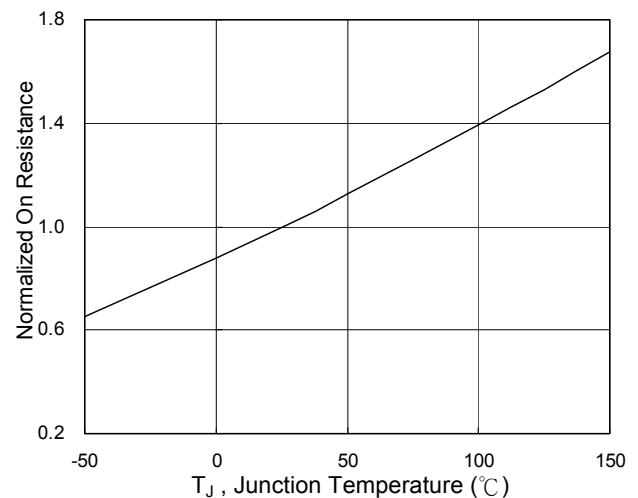


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

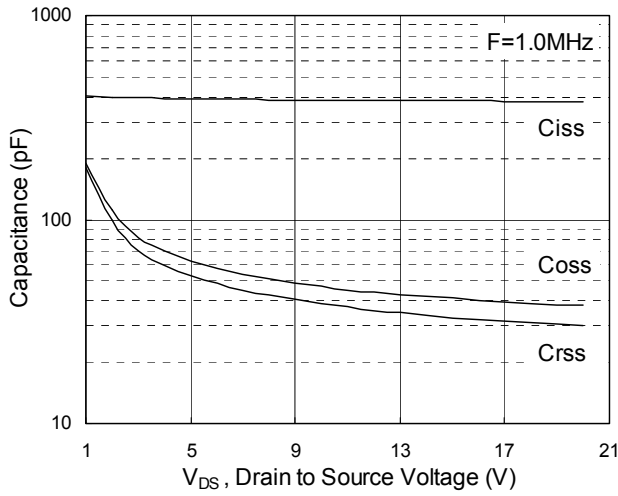


Fig.7 Capacitance

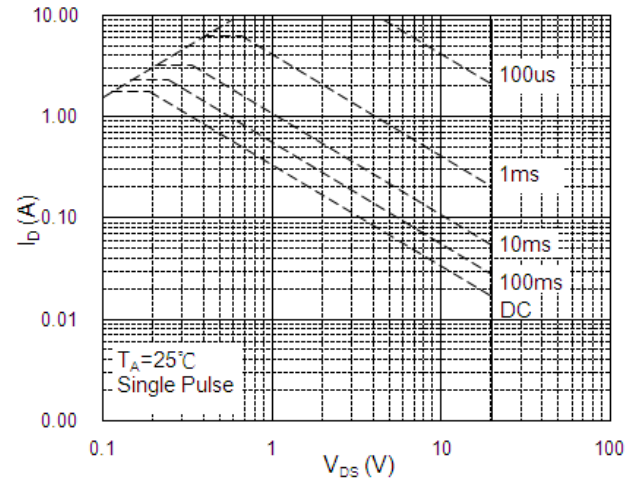


Fig.8 Safe Operating Area

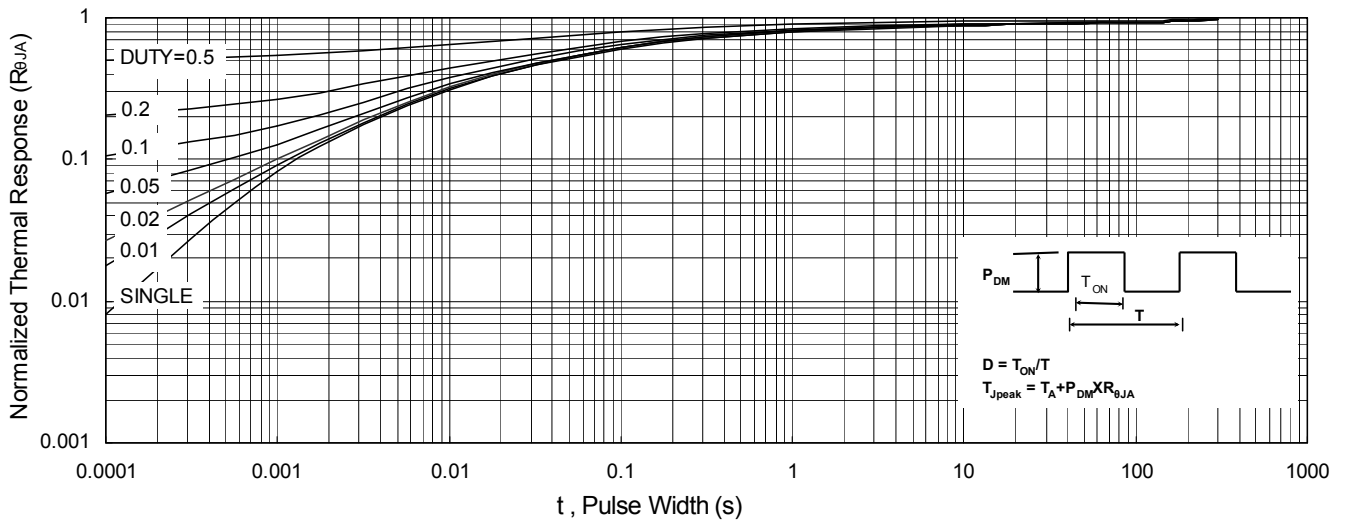


Fig.9 Normalized Maximum Transient Thermal Impedance

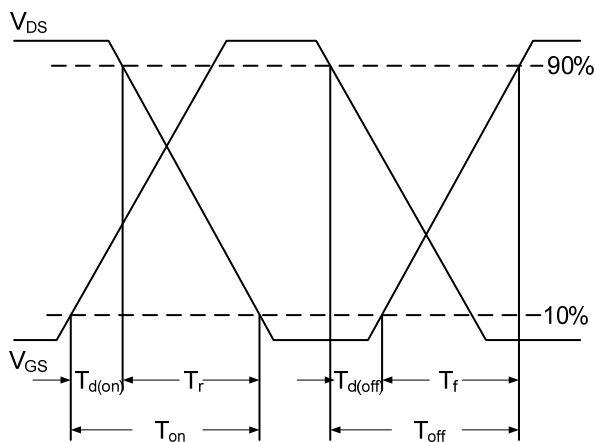


Fig.10 Switching Time Waveform

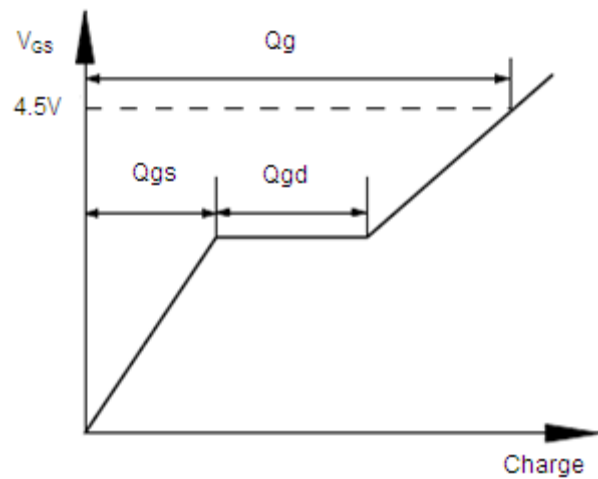
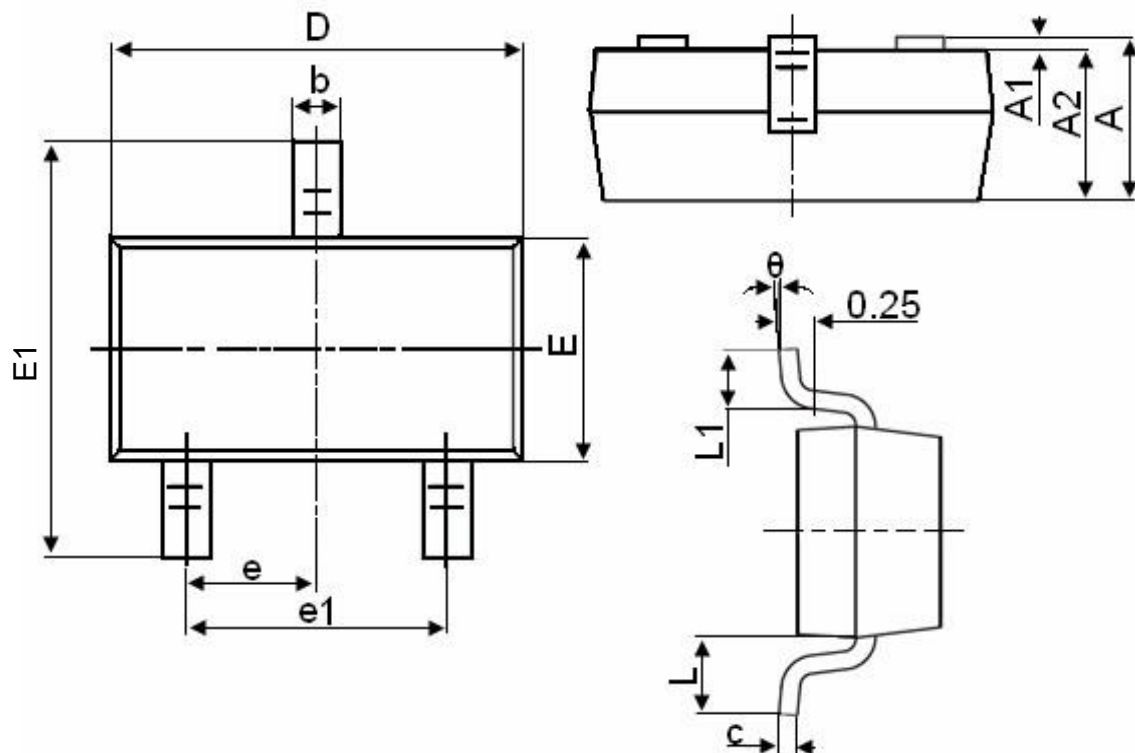


Fig.11 Gate Charge Waveform

Packaging information


Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°